SIPMOS® Small-Signal-Transistor

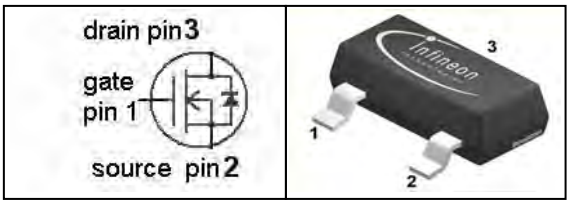
Feature

- N-Channel
- Enhancement mode
- Logic level
- d*v*/d*t* rated

Product Summary

V_{DS}	240	V
$R_{DS(on),max}$	14	Ω
I_D	0.1	A

SOT-23



Type	Package	Ordering Code	Tape and Reel Information	Marking
BSS131	SOT23	Q62702-S565	E6327	SRs
BSS131	SOT23	Q67000-S229	E6433	SRs

Maximum ratings, at T_j=25 °C, unless otherwise specified

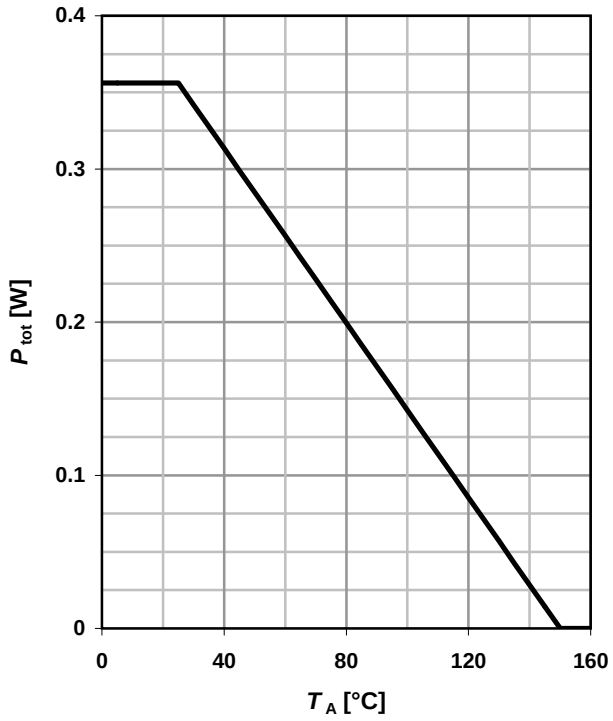
Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_A=25 °C	0.11	A
		T_A=70 °C	0.09	
Pulsed drain current	$I_{D,pulse}$	T_A=25 °C	0.4	
Reverse diode d*v*/d*t*	d*v*/d*t*	I_D=0.1 A, V_{DS}=192 V, d*i*/d*t*=200 A/µs, $T_{j,max}$=150 °C	6	kV/µs
Gate source voltage	V_{GS}		±20	V
ESD sensitivity (HBM) as per MIL-STD 883			Class 1	
Power dissipation	P_{tot}	T_A=25 °C	0.36	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - minimal footprint	R_{thJA}		-	-	350	K/W
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=250 µA	240	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=0 V, I_D=56 µA	0.8	1.4	1.8	
Drain-source leakage current	$I_{D\ (off)}$	V_{DS}=240 V, V_{GS}=0 V, T_j=25 °C	-	-	0.01	µA
		V_{DS}=240 V, V_{GS}=0 V, T_j=150 °C	-	-	5	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	-	10	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=4.5 V, I_D=0.09 A	-	9.07	20	Ω
		V_{GS}=10 V, I_D=0.1 A	-	7.7	14	
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=0.08 A	0.06	0.13	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=25 V, f=1 MHz	-	58	77	pF
Output capacitance	C_{oss}		-	7.3	10	
Reverse transfer capacitance	C_{rss}		-	2.8	4.2	
Turn-on delay time	$t_{d(on)}$	V_{DD}=120 V, V_{GS}=10 V, I_D=0.1 A, R_G=6 Ω	-	3.3	5.0	ns
Rise time	t_r		-	3.1	4.6	
Turn-off delay time	$t_{d(off)}$		-	13.7	20	
Fall time	t_f		-	64.5	97	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=192 V, I_D=0.1 A, V_{GS}=0 to 10 V	-	0.16	0.22	nC
Gate to drain charge	Q_{gd}		-	0.8	1.2	
Gate charge total	Q_g		-	2.1	3.1	
Gate plateau voltage	$V_{plateau}$		-	2.90	-	V
Reverse Diode						
Diode continous forward current	I_S	T_A=25 °C	-	-	0.11	A
Diode pulse current	$I_{S,pulse}$		-	-	0.43	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=0.1 A, T_j=25 °C	-	0.81	1.2	V
Reverse recovery time	t_{rr}	V_R=120 V, I_F=0.1 A, di_F/dt=100 A/µs	-	42.9	64.3	ns
Reverse recovery charge	Q_{rr}		-	22.6	34	nC

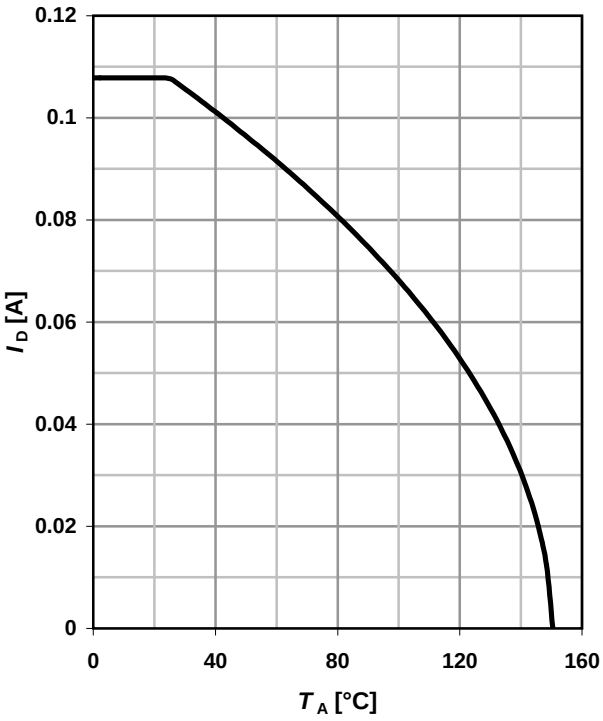
1 Power dissipation

$P_{tot}=f(T_A)$



2 Drain current

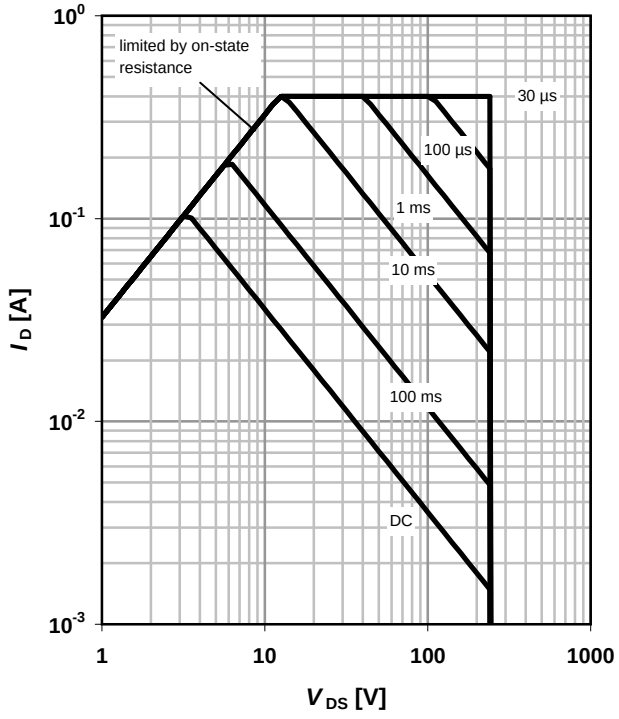
$I_D=f(T_A)$; $V_{GS}\geq 10$ V



3 Safe operating area

$I_D=f(V_{DS})$; $T_A=25$ °C; $D=0$

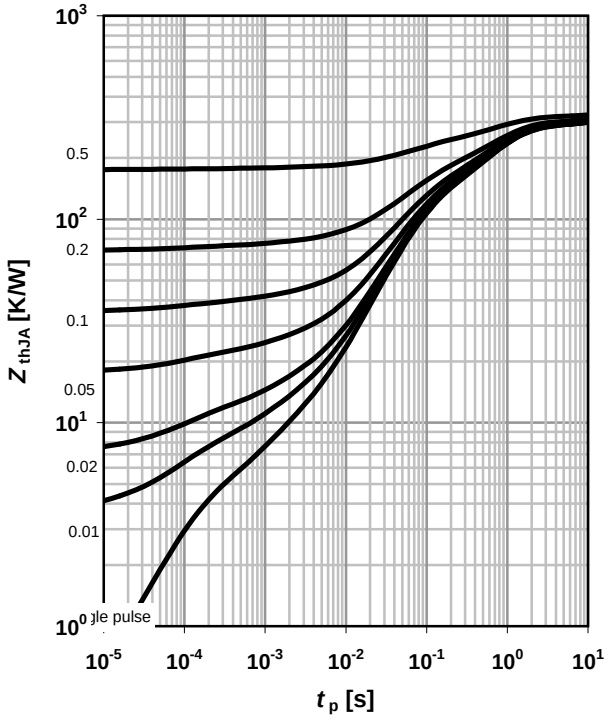
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJA}=f(t_p)$

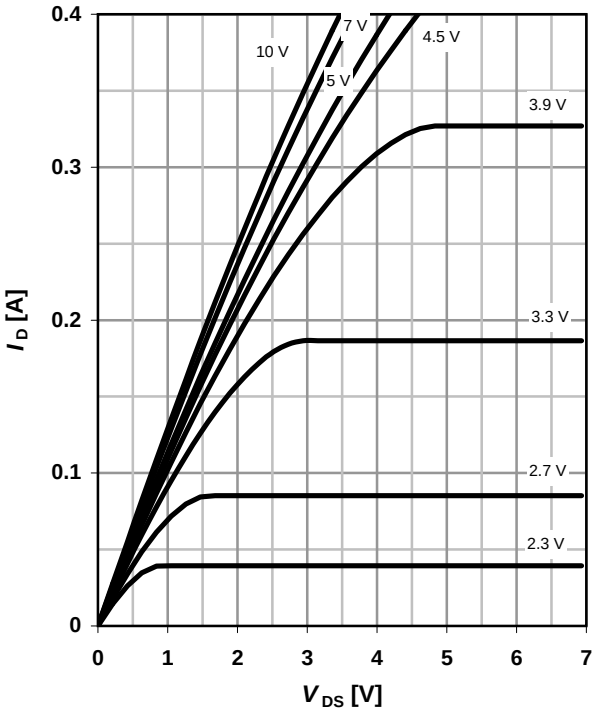
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D=f(V_{DS})$; $T_j=25$ °C

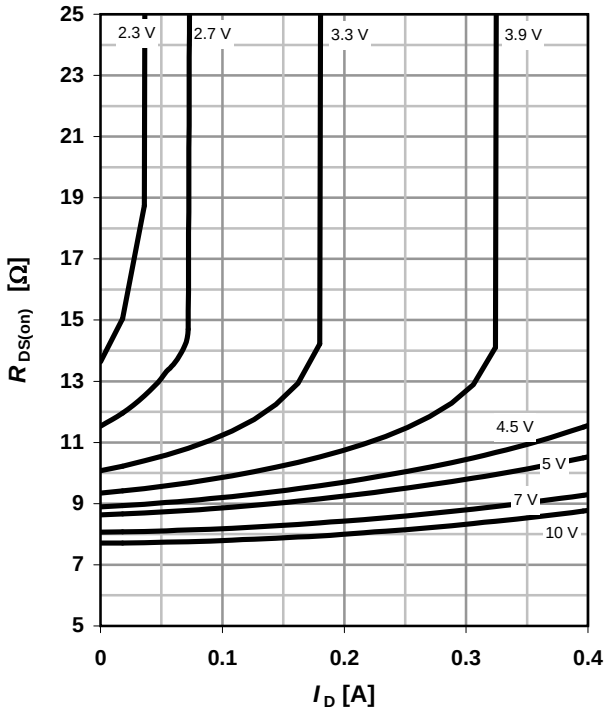
parameter: V_{GS}



6 Typ. drain-source on resistance

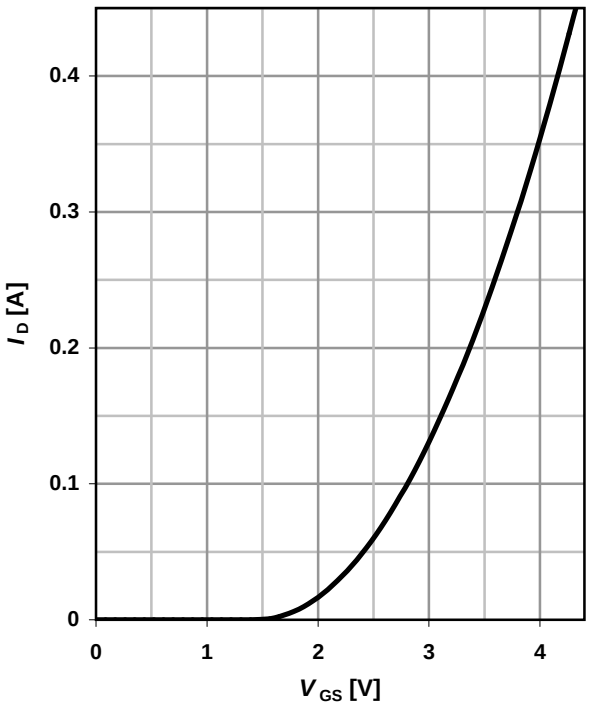
$R_{DS(on)}=f(I_D)$; $T_j=25$ °C

parameter: V_{GS}



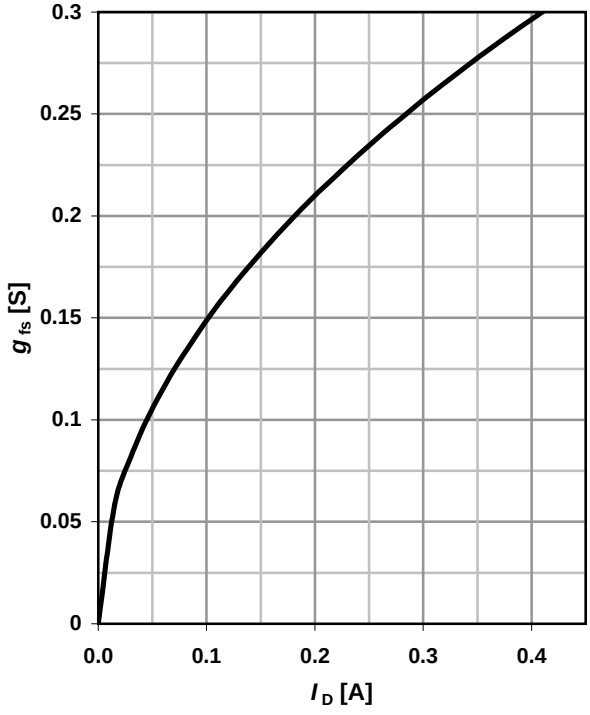
7 Typ. transfer characteristics

$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$



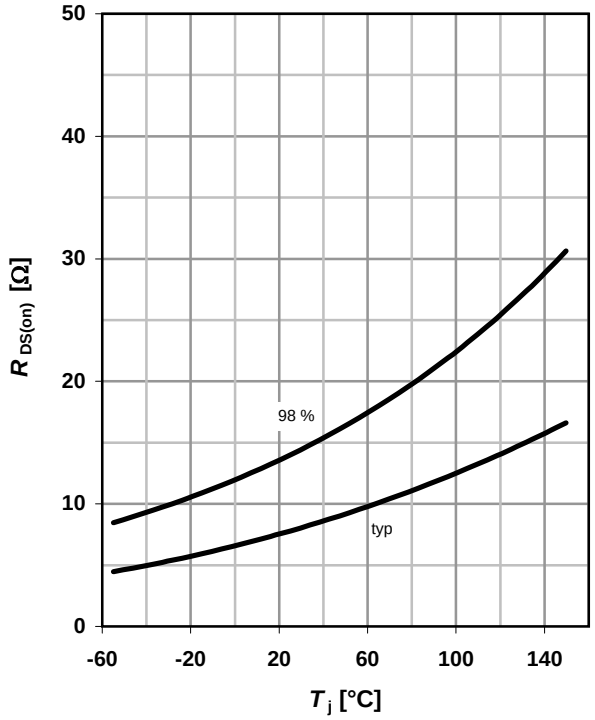
8 Typ. forward transconductance

$g_{fs}=f(I_D)$; $T_j=25$ °C



9 Drain-source on-state resistance

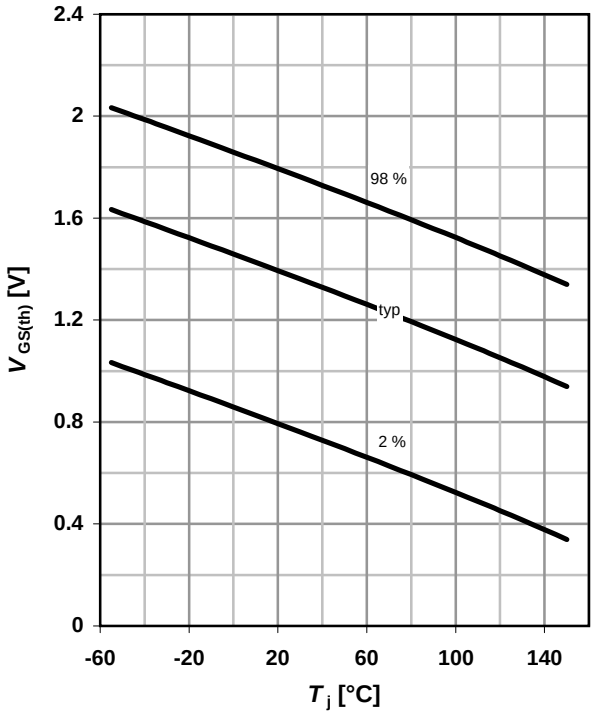
$R_{DS(on)}=f(T_j)$; $I_D=0.1$ A; $V_{GS}=10$ V



10 Typ. gate threshold voltage

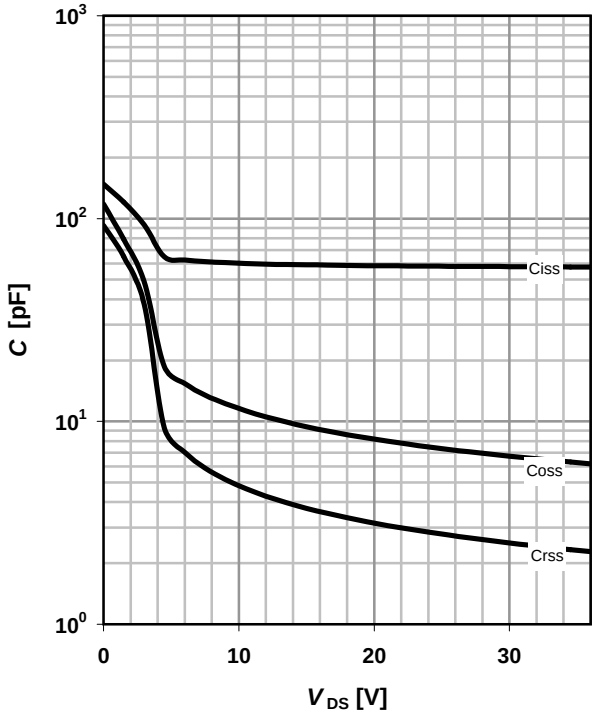
$V_{GS(th)}=f(T_j)$; $V_{DS}=V_{GS}$; $I_D=56$ µA

parameter: I_D



11 Typ. capacitances

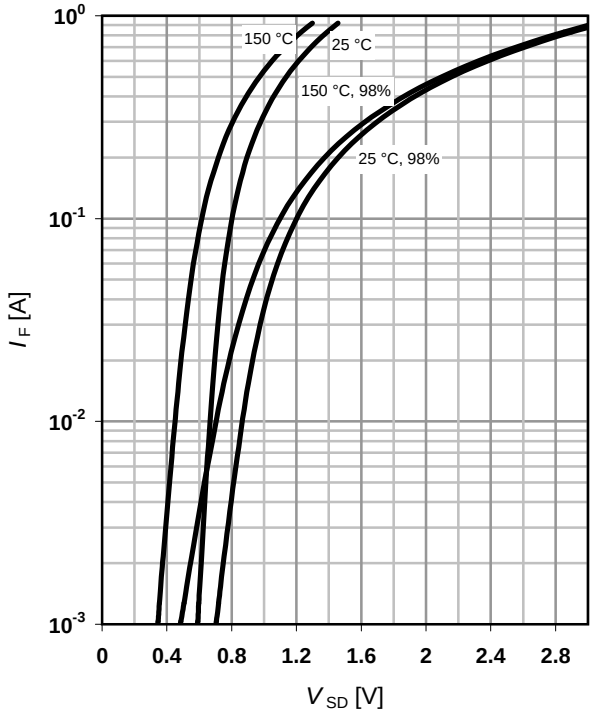
$C=f(V_{DS})$; $V_{GS}=0$ V; $f=1$ MHz; $T_j=25$°C



12 Forward characteristics of reverse diode

$I_F=f(V_{SD})$

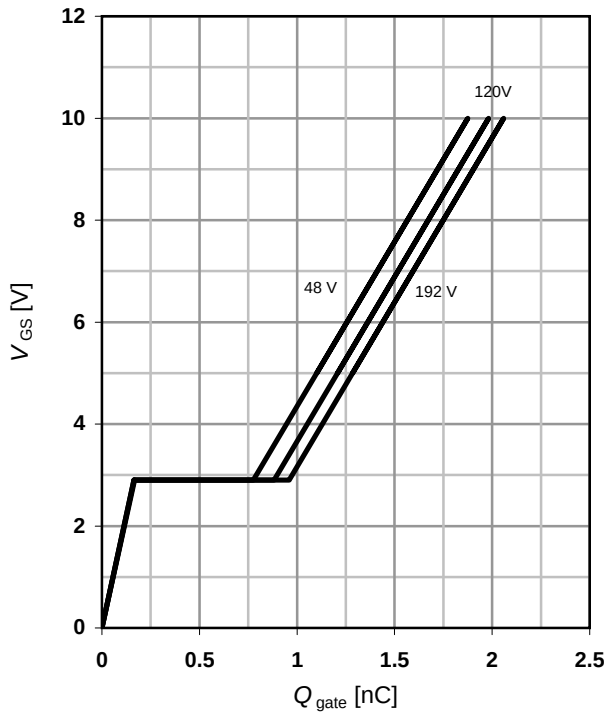
parameter: T_j



13 Typ. gate charge

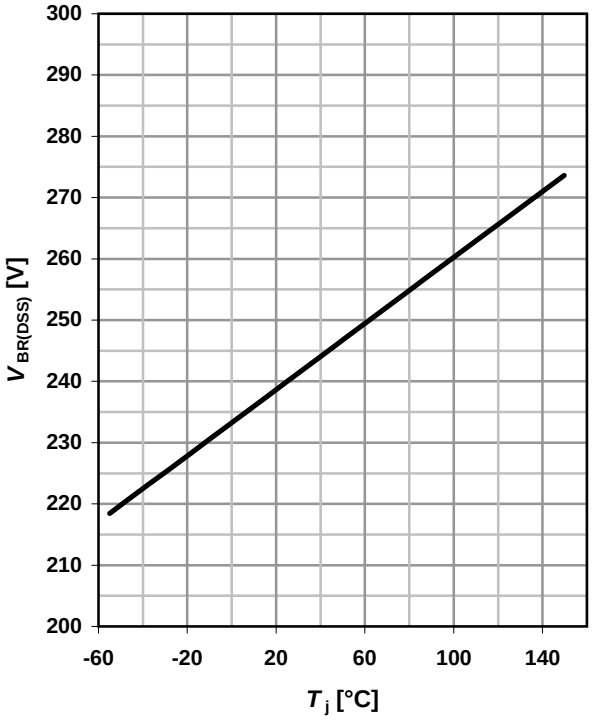
V_{GS}=f(Q_{gate}); I_D=0.1 A pulsed

parameter: V_{DD}

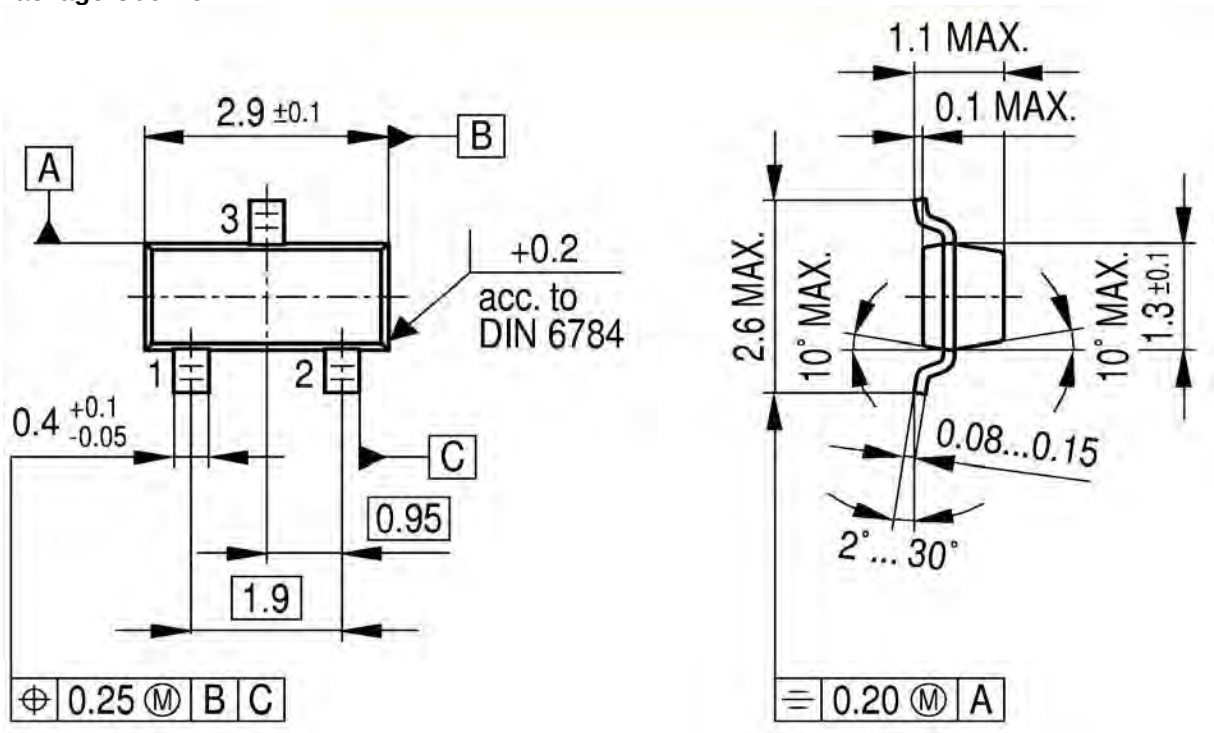


14 Drain-source breakdown voltage

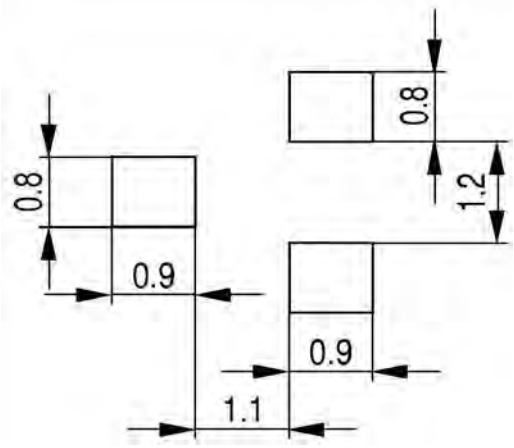
$V_{BR(DSS)}$=f(T_j); I_D=250 µA



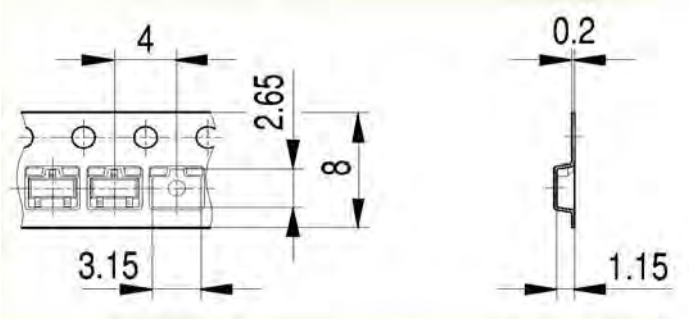
Package Outline:



Footprint:



Packaging:



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